N-Channel 60 V (D-S) MOSFET

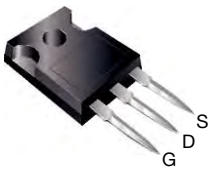
PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0016
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0020
I_D (A)	270
Configuration	Single

FEATURES

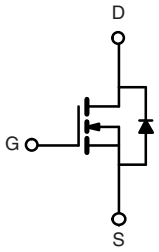
- Trench power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested

RoHS COMPLIANT
HALOGEN FREE

TO-247AC



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C	I_D	270	A
	T_C = 125 °C		120 [a]	
Continuous Source Current (Diode Conduction)		I_S	120 [a]	
Pulsed Drain Current [b]		I_{DM}	600	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	75	
Single Pulse Avalanche Energy		E_{AS}	281	mJ
Maximum Power Dissipation [b]	T_C = 25 °C	P_D	375	W
	T_C = 125 °C		125	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Junction-to-Ambient	PCB Mount [c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	

Notes

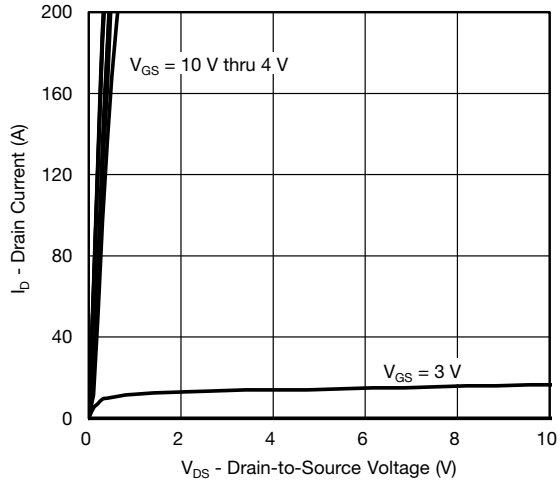
a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR4 material).

SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		1.5	2.0	2.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 60 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 175 °C	-	-	1.5	mA
On-State Drain Current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 30 A	-	0.0016	-	Ω
		V_{GS} = 10 V	I_D = 30 A, T_J = 125 °C	-	0.0031	-	
		V_{GS} = 10 V	I_D = 30 A, T_J = 175 °C	-	0.0037	-	
		V_{GS} = 4.5 V	I_D = 20 A	-	0.0020	-	
Forward Transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 30 A		-	164	-	S
Dynamic [b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	12 060	15 100	pF
Output Capacitance	C_{oss}			-	5750	7200	
Reverse Transfer Capacitance	C_{rss}			-	860	1100	
Total Gate Charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 30 V, I_D = 80 A	-	128	200	nC
Gate-Source Charge [c]	Q_{gs}			-	33	-	
Gate-Drain Charge [c]	Q_{gd}			-	11	-	
Gate Resistance	R_g	f = 1 MHz		0.8	1.68	2.6	Ω
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.375 Ω I_D ≅ 80 A, V_{GEN} = 10 V, R_g = 1 Ω		-	20	25	ns
Rise Time [c]	t_r			-	15	40	
Turn-Off Delay Time [c]	$t_{d(off)}$			-	65	100	
Fall Time [c]	t_f			-	12	20	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed Current [a]	I_{SM}			-	-	300	A
Forward Voltage	V_{SD}	I_F = 80 A, V_{GS} = 0 V		-	0.88	1.5	V

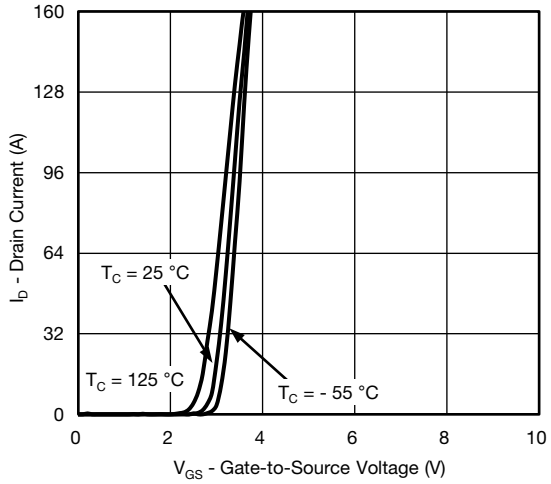
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

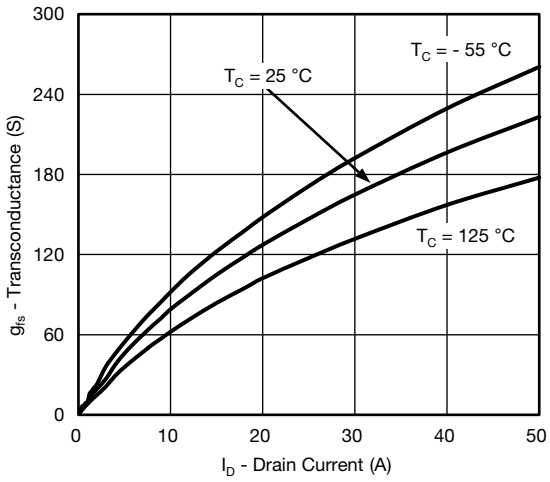
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



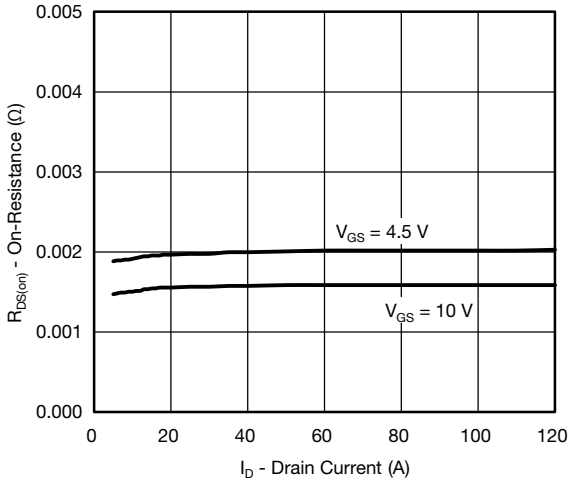
Output Characteristics



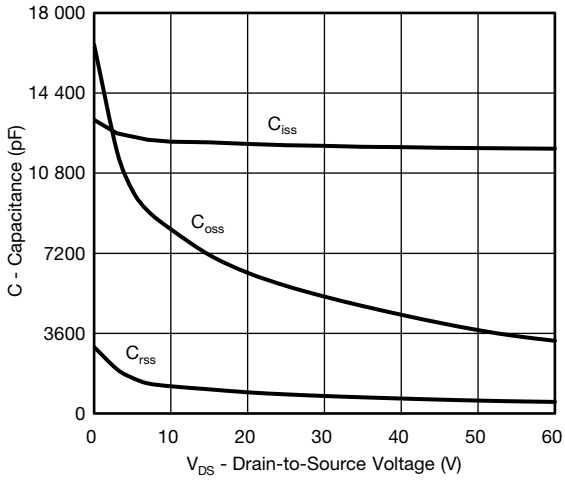
Transfer Characteristics



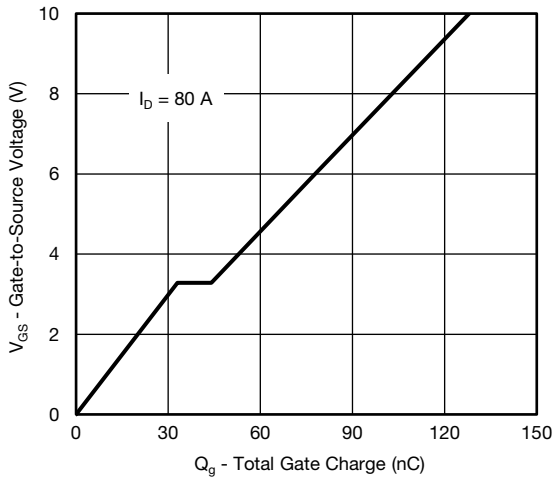
Transconductance



On-Resistance vs. Drain Current

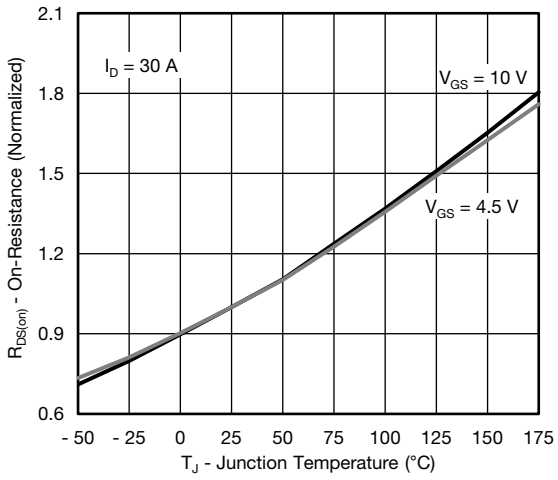


Capacitance

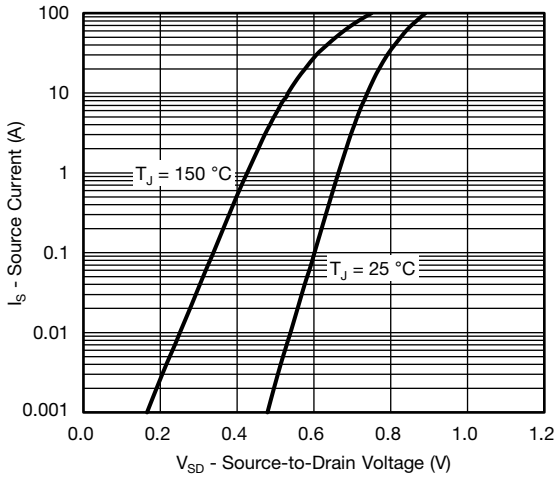


Gate Charge

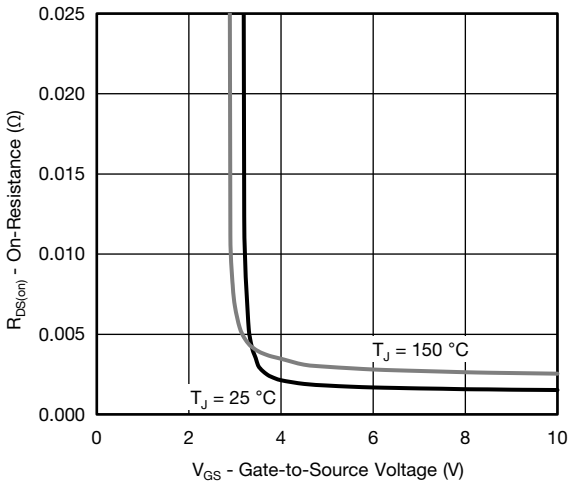
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



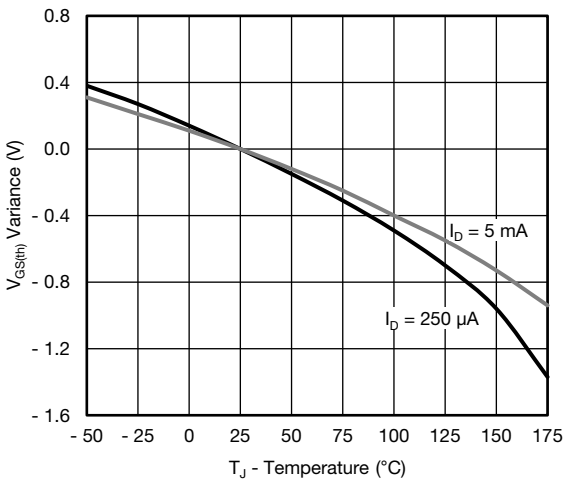
On-Resistance vs. Junction Temperature



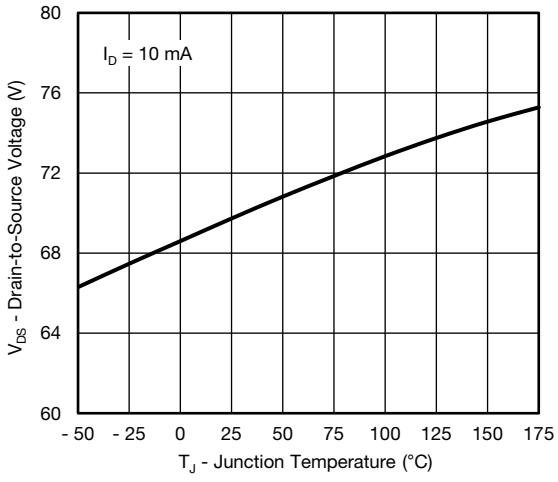
Source Drain Diode Forward Voltage



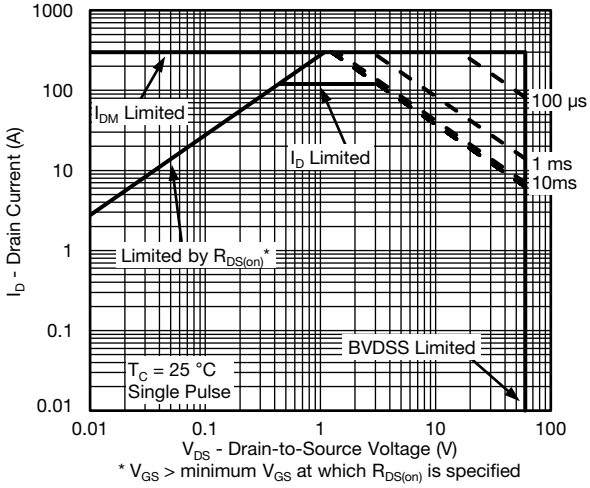
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

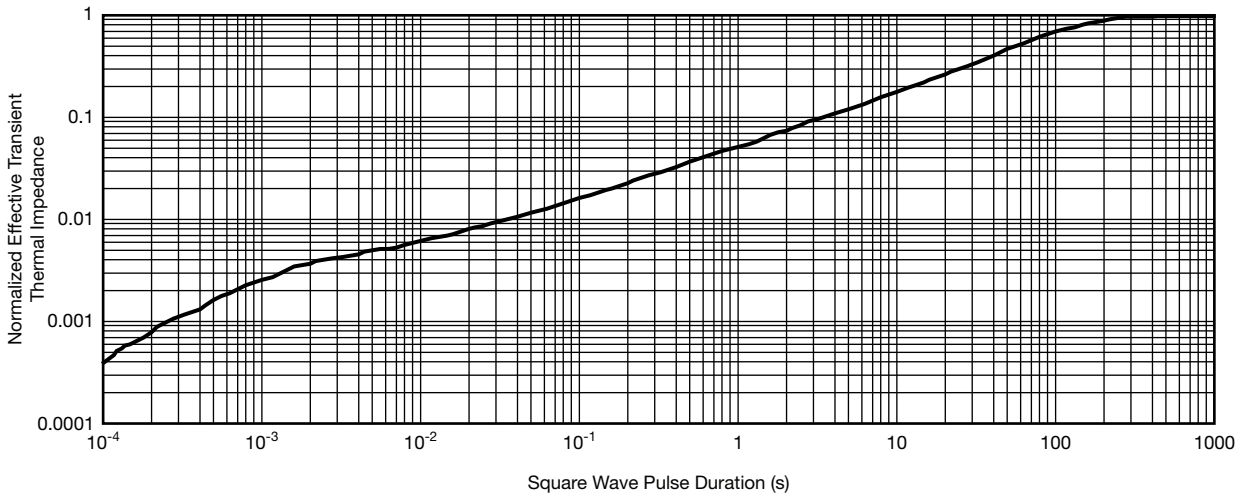


Drain Source Breakdown vs. Junction Temperature

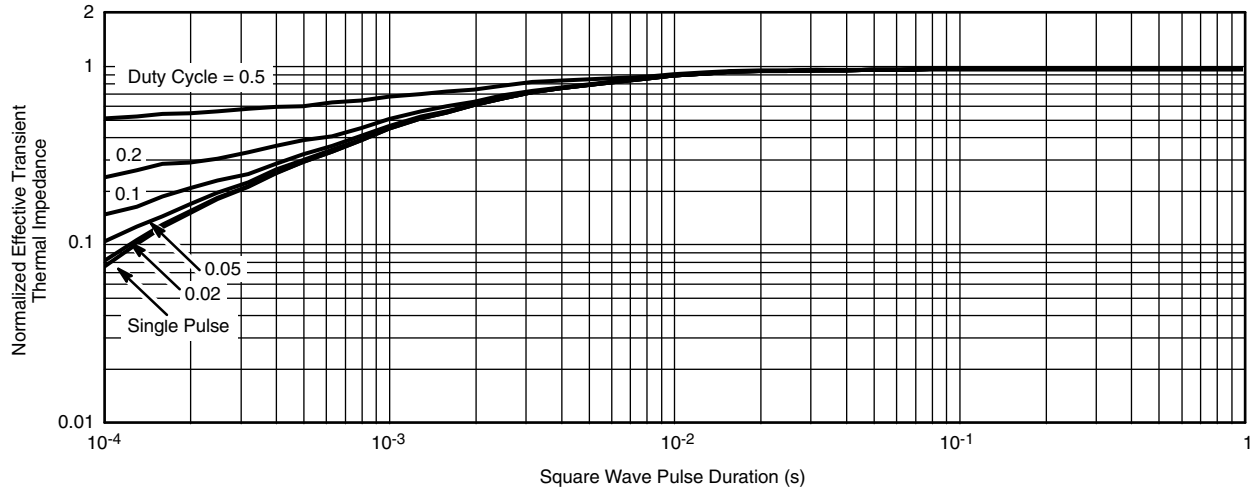


Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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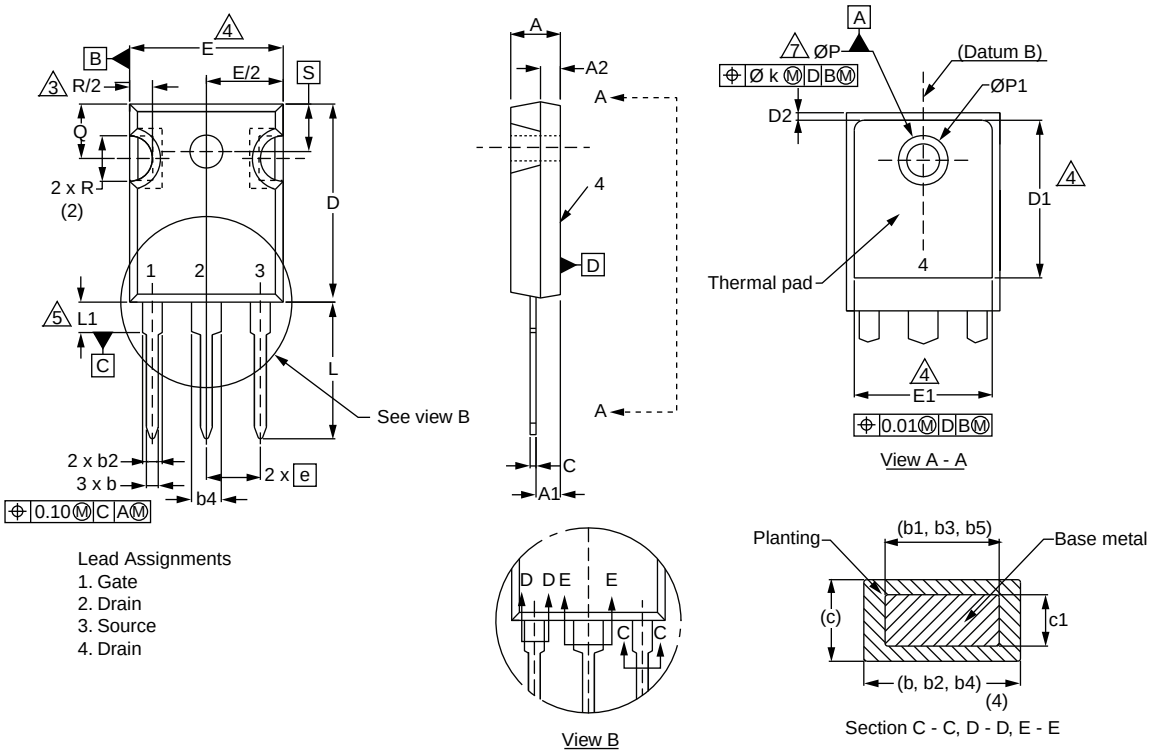

Lead Assignments
1. Gate
2. Drain
3. Source
4. Drain

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.58	5.31	0.180	0.209
A1	2.21	2.59	0.087	0.102
A2	1.17	2.49	0.046	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.53	2.39	0.060	0.094
b3	1.65	2.37	0.065	0.093
b4	2.42	3.43	0.095	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.82	0.776	0.820
D1	13.08	-	0.515	-

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.25	0.559	0.640
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.51	3.66	0.138	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

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